



# Thyristor Module

$V_{RRM} = 2 \times 1200 \text{ V}$

$I_{TAV} = 250 \text{ A}$

$V_T = 1,08 \text{ V}$

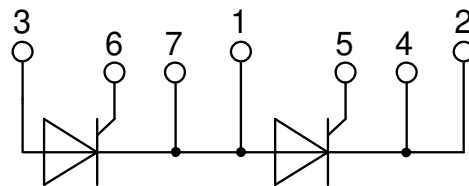
Phase leg

Part number

**MCC255-12io1**



Backside: isolated



### Features / Advantages:

- International standard package
- Direct copper bonded Al<sub>2</sub>O<sub>3</sub>-ceramic with copper base plate
- Planar passivated chip
- Keyed gate/cathode twin pins

### Applications:

- Motor control, softstarter
- Power converter
- Heat and temperature control for industrial furnaces and chemical processes
- Lighting control
- Solid state switches

### Package: Y1

- Isolation Voltage: 4800 V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Base plate: Copper internally DCB isolated
- Advanced power cycling

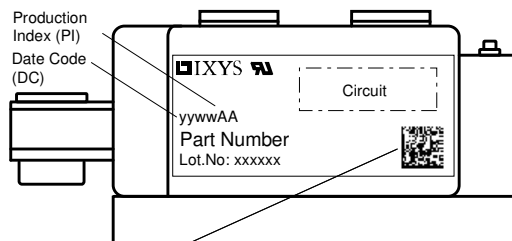
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Thyristor				Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit	
$V_{RSM/DSM}$	max. non-repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}C$			1300	V	
$V_{RRM/DRM}$	max. repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}C$			1200	V	
$I_{RD}$	reverse current, drain current	$V_{R/D} = 1200 V$	$T_{VJ} = 25^{\circ}C$		1	mA	
		$V_{R/D} = 1200 V$	$T_{VJ} = 140^{\circ}C$		40	mA	
$V_T$	forward voltage drop	$I_T = 300 A$	$T_{VJ} = 25^{\circ}C$		1,14	V	
		$I_T = 600 A$			1,36	V	
		$I_T = 300 A$	$T_{VJ} = 125^{\circ}C$		1,08	V	
		$I_T = 600 A$			1,33	V	
$I_{TAV}$	average forward current	$T_C = 85^{\circ}C$	$T_{VJ} = 140^{\circ}C$		250	A	
$I_{T(RMS)}$	RMS forward current	180° sine			450	A	
$V_{T0}$	threshold voltage	} for power loss calculation only	$T_{VJ} = 140^{\circ}C$		0,80	V	
$r_T$	slope resistance				0,68	mΩ	
$R_{thJC}$	thermal resistance junction to case				0,14	K/W	
$R_{thCH}$	thermal resistance case to heatsink			0,04		K/W	
$P_{tot}$	total power dissipation		$T_C = 25^{\circ}C$		820	W	
$I_{TSM}$	max. forward surge current	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}C$		9,20	kA	
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$	$V_R = 0 V$		9,94	kA	
		$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$	$T_{VJ} = 140^{\circ}C$		7,82	kA	
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$	$V_R = 0 V$		8,45	kA	
$I^2t$	value for fusing	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}C$		423,2	kA <sup>2</sup> s	
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$	$V_R = 0 V$		410,6	kA <sup>2</sup> s	
		$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$	$T_{VJ} = 140^{\circ}C$		305,8	kA <sup>2</sup> s	
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$	$V_R = 0 V$		296,7	kA <sup>2</sup> s	
$C_J$	junction capacitance	$V_R = 400V \quad f = 1 \text{ MHz}$	$T_{VJ} = 25^{\circ}C$	438		pF	
$P_{GM}$	max. gate power dissipation	$t_p = 30 \mu s$	$T_C = 140^{\circ}C$		120	W	
		$t_p = 500 \mu s$			60	W	
$P_{GAV}$	average gate power dissipation				20	W	
$(di/dt)_{cr}$	critical rate of rise of current	$T_{VJ} = 140^{\circ}C; f = 50 \text{ Hz}$ repetitive, $I_T = 860 A$			100	A/μs	
		$t_p = 200 \mu s; di_G/dt = 1 A/\mu s;$ $I_G = 1 A; V_D = \frac{2}{3} V_{DRM}$ non-repet., $I_T = 250 A$			500	A/μs	
$(dv/dt)_{cr}$	critical rate of rise of voltage	$V_D = \frac{2}{3} V_{DRM}$ $R_{GK} = \infty$ ; method 1 (linear voltage rise)	$T_{VJ} = 140^{\circ}C$		1000	V/μs	
$V_{GT}$	gate trigger voltage	$V_D = 6 V$	$T_{VJ} = 25^{\circ}C$		2	V	
			$T_{VJ} = -40^{\circ}C$		3	V	
$I_{GT}$	gate trigger current	$V_D = 6 V$	$T_{VJ} = 25^{\circ}C$		150	mA	
			$T_{VJ} = -40^{\circ}C$		220	mA	
$V_{GD}$	gate non-trigger voltage	$V_D = \frac{2}{3} V_{DRM}$	$T_{VJ} = 140^{\circ}C$		0,25	V	
$I_{GD}$	gate non-trigger current				10	mA	
$I_L$	latching current	$t_p = 30 \mu s$	$T_{VJ} = 25^{\circ}C$		200	mA	
		$I_G = 0,45 A; di_G/dt = 0,45 A/\mu s$					
$I_H$	holding current	$V_D = 6 V \quad R_{GK} = \infty$	$T_{VJ} = 25^{\circ}C$		150	mA	
$t_{gd}$	gate controlled delay time	$V_D = \frac{1}{2} V_{DRM}$	$T_{VJ} = 25^{\circ}C$		2	μs	
		$I_G = 1 A; di_G/dt = 1 A/\mu s$					
$t_q$	turn-off time	$V_R = 100 V; I_T = 300 A; V_D = \frac{2}{3} V_{DRM}$ $di/dt = 10 A/\mu s; dv/dt = 50 V/\mu s; t_p = 200 \mu s$	$T_{VJ} = 125^{\circ}C$	200		μs	

Package Y1		Ratings				
Symbol	Definition	Conditions	min.	typ.	max.	Unit
$I_{RMS}$	RMS current	per terminal			600	A
$T_{VJ}$	virtual junction temperature		-40		140	°C
$T_{op}$	operation temperature		-40		125	°C
$T_{stg}$	storage temperature		-40		125	°C
<b>Weight</b>				680		g
$M_D$	mounting torque		4,5		7	Nm
$M_T$	terminal torque		11		13	Nm
$d_{Spp/App}$	creepage distance on surface   striking distance through air	terminal to terminal	16,0			mm
$d_{Spb/Apb}$		terminal to backside	16,0			mm
$V_{ISOL}$	isolation voltage	t = 1 second	4800			V
		t = 1 minute	4000			V

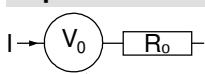


Data Matrix: part no. (1-19), DC + PI (20-25), lot.no.# (26-31), blank (32), serial no.# (33-36)

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MCC255-12io1	MCC255-12io1	Box	3	509922

**Equivalent Circuits for Simulation**

\* on die level

 $T_{VJ} = 140^{\circ}\text{C}$ 

**Thyristor**

$V_{0\ max}$	threshold voltage	0,8	V
$R_{0\ max}$	slope resistance *	0,5	mΩ



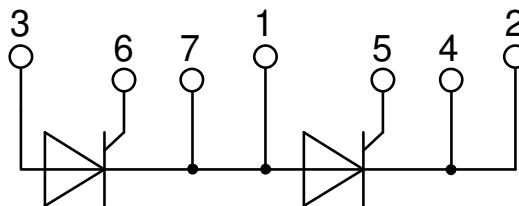
**Outlines Y1**



**Optional accessories for modules**

Keyed gate/cathode twin plugs with wire length = 350 mm, gate = white, cathode = red

Type ZY 180L (L = Left for pin pair 4/5)  
 Type ZY 180R (R = Right for pin pair 6/7) } UL 758, style 3751



**Thyristor**



Fig. 1 Surge overload current  
 $I_{T(F)SM}$ : Crest value, t: duration



Fig. 2  $I^2dt$  versus time



Fig. 3 Max. forward current at case temperature



Fig. 4 Power dissipation versus on-state current and ambient temperature (per thyristor or diode)

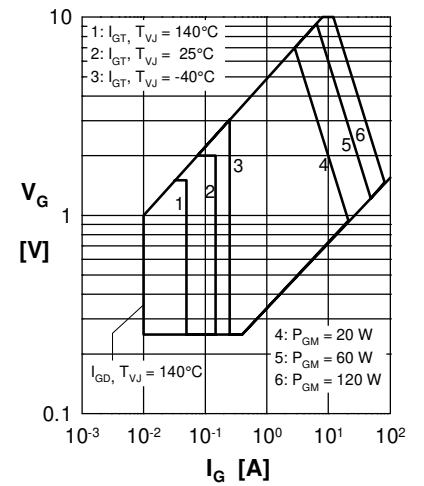


Fig. 5 Surge overload current  
 $I_{T(F)SM}$ : Crest value, t: duration



Fig. 6 Three phase rectifier bridge: Power dissipation vs. direct output current and ambient temperature



Fig. 7 Gate trigger delay time



**Thyristor**

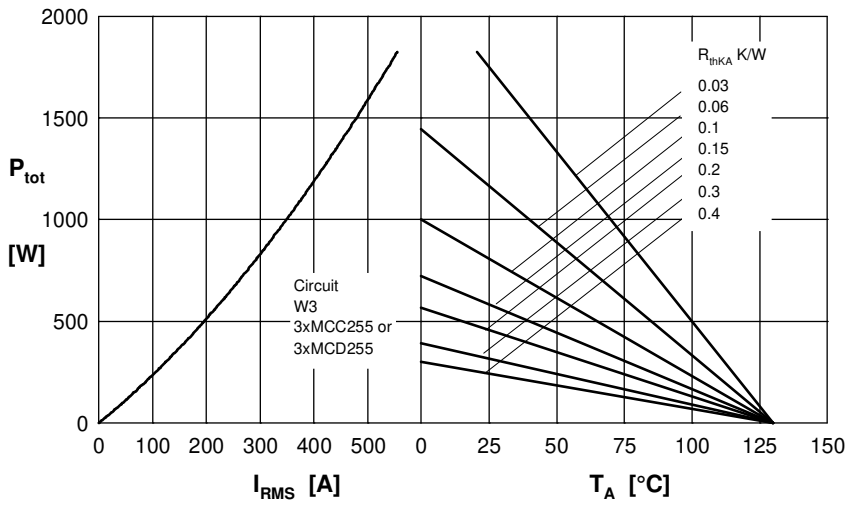


Fig. 8 Three phase AC-controller: Power dissipation versus  $R_{MS}$  output current and ambient temperature

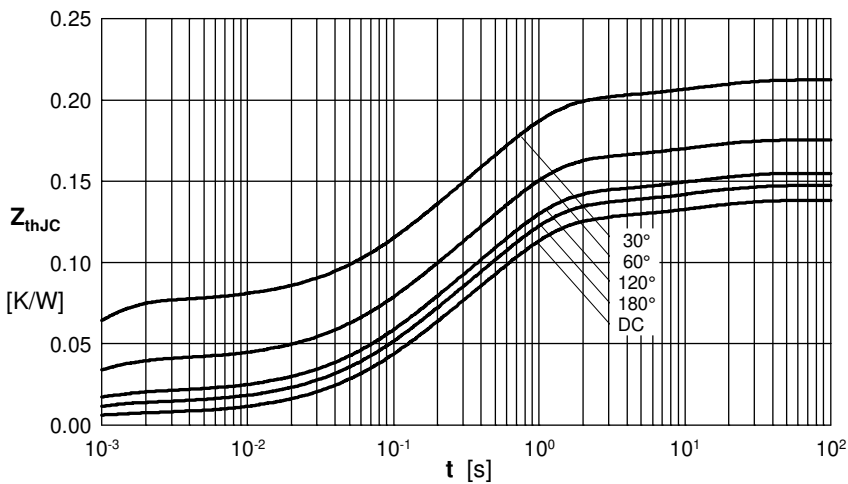


Fig. 9 Transient thermal impedance junction to case (per thyristor/diode)

$R_{thJC}$  for various conduct. angles d:

d	$R_{thJC}$ [K/W]
DC	0.139
180°	0.148
120°	0.156
60°	0.176
30°	0.214

Constants for  $Z_{thJC}$  calculation:

i	$R_{thi}$ [K/W]	$t_i$ [s]
1	0.0066	0.00054
2	0.0358	0.098
3	0.0831	0.54
4	0.0129	12

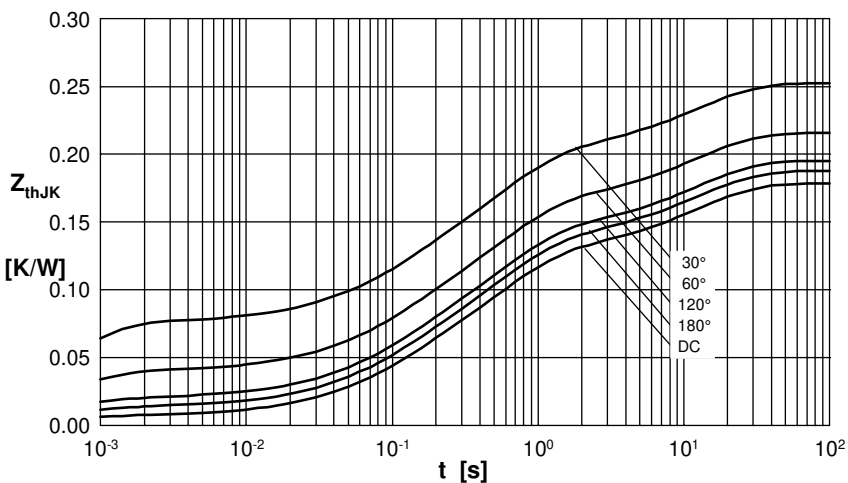


Fig. 10 Transient thermal impedance junction to heatsink (per thyristor/diode)

$R_{thJK}$  for various conduct. angles d:

d	$R_{thJK}$ [K/W]
DC	0.179
180°	0.188
120°	0.196
60°	0.216
30°	0.254

Constants for  $Z_{thJK}$  calculation:

i	$R_{thi}$ [K/W]	$t_i$ [s]
1	0.0066	0.00054
2	0.0358	0.098
3	0.0831	0.54
4	0.0129	12
5	0.04	12